

## isc Silicon NPN Power Transistor

#### **DESCRIPTION**

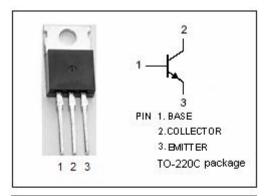
- · Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= 1.0V(Max.)@I<sub>C</sub>= 3A
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

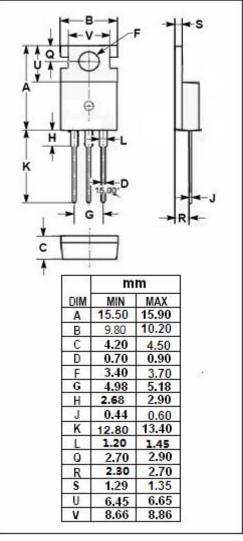
### **APPLICATIONS**

 Designed for switching regulator, DC-DC converter and high frequency power amplifier applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	7	Α
Ісм	Collector Current-Peak	15	Α
l <sub>Β</sub>	Base Current-Continuous	3.5	Α
Pc	P <sub>C</sub> Collector Power Dissipation @ T <sub>C</sub> =25°C		W
TJ	T <sub>J</sub> Junction Temperature		${\mathbb C}$
T <sub>stg</sub>	T <sub>stg</sub> Storage Temperature Range		${\mathbb C}$







## **isc Silicon NPN Power Transistor**

2SC3158

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

10-20 C U	illess otherwise specified					
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A; L= 1mH	400			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 400V; I <sub>E</sub> = 0			10	μ <b>А</b>
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 400V;V <sub>BE(off)</sub> =-1.5V V <sub>CE</sub> = 400V;V <sub>BE(off)</sub> =-1.5V,T <sub>a</sub> =125°C			10 1.0	μA mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	20		80	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	20		80	
h <sub>FE-3</sub>	DC Current Gain	Ic= 3A; Vc== 5V	10			
Switching ti	mes	7	1	1		
ton	Turn-On Time				1.0	μS
t <sub>stg</sub>	Storage Time	$I_C$ = 3A; $I_{B1}$ = - $I_{B2}$ = 0.6A; $R_L$ = 50 $\Omega$ ; $V_{CC}$ $\approx$ 150V			2.5	μS
t <sub>f</sub>	Fall Time				1.0	μs

### ♦ h<sub>FE-2</sub> Classifications

M	L	K
20-40	30-60	40-80

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